

## CLAIMS

What is claimed is:

1. (Currently Amended) A layered article, comprising:  
a single crystal silicon comprising substrate;  
a silicon oxynitride layer (SixNyOz) disposed on said silicon substrate, and  
a single crystal group III-nitride layer disposed on and in contact with said oxynitride layer, wherein a thickness of said silicon oxynitride layer is less than 100 angstroms.
2. (Original) The article of claim 1, wherein said silicon substrate is (111) oriented.
3. (Original) The article of claim 2, wherein said single crystal group III-nitride layer is a GaN layer.
4. (Currently amended) The article of claim 1, wherein [[a]] said thickness of said silicon oxynitride layer is from 15 to 40 angstroms.
5. (Original) The article of claim 1, further comprising an integrated electronic circuit built on said article.
6. (Original) The article of claim 1, further comprising an integrated optical or optoelectronic device built on said article.

7. (Cancelled)

8. (Cancelled)

9. (Cancelled)

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

14. (Cancelled)

15. (Cancelled)

16. (Cancelled)

17. (Currently amended) The article of claim 1, wherein [[a]] said thickness of said silicon oxynitride layer is from 15 to 50 angstroms.